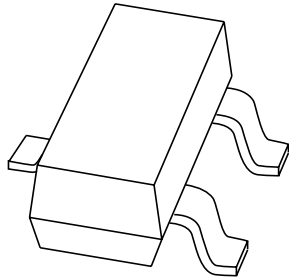


# DATA SHEET



## **BAV199** Low-leakage double diode

Product specification

## Low-leakage double diode

## BAV199

## FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8  $\mu$ s
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

## APPLICATION

- Low-leakage current applications in surface mounted circuits.

## DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small SOT23 plastic SMD package. The diodes are connected in series.

## MARKING

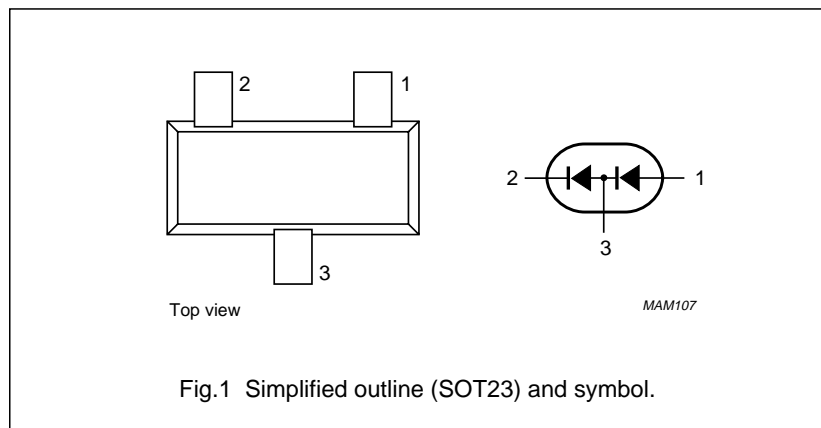
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BAV199	JY*

## Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

## PINNING

PIN	DESCRIPTION
1	anode
2	cathode
3	anode; cathode



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per diode</b>					
$V_{RRM}$	repetitive peak reverse voltage		–	85	V
$V_R$	continuous reverse voltage		–	75	V
$I_F$	continuous forward current	single diode loaded; note 1; see Fig.2	–	160	mA
		double diode loaded; note 1; see Fig.2	–	140	mA
$I_{FRM}$	repetitive peak forward current		–	500	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge; see Fig.4			
		$t_p = 1\text{ }\mu\text{s}$	–	4	A
		$t_p = 1\text{ ms}$	–	1	A
		$t_p = 1\text{ s}$	–	0.5	A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ }^\circ\text{C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	junction temperature		–	150	$^\circ\text{C}$

## Note

1. Device mounted on a FR4 printed-circuit board.

## Low-leakage double diode

BAV199

**ELECTRICAL CHARACTERISTICS** $T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
<b>Per diode</b>					
$V_F$	forward voltage	see Fig.3			
		$I_F = 1\text{ mA}$	–	900	mV
		$I_F = 10\text{ mA}$	–	1000	mV
		$I_F = 50\text{ mA}$	–	1100	mV
		$I_F = 150\text{ mA}$	–	1250	mV
$I_R$	reverse current	see Fig.5			
		$V_R = 75\text{ V}$	0.003	5	nA
		$V_R = 75\text{ V}; T_j = 150\text{ °C}$	3	80	nA
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.6	2	–	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}; R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	0.8	3	$\mu\text{s}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

**Note**

1. Device mounted on a FR4 printed-circuit board.

Low-leakage double diode

BAV199

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23

